Microsemi
SCOTTSDALE DIVISION

USB0803C-A thru USB0824C-A, e3

Bidirectional TVSarray ™

Replaced by USB50803C-A thru USB50824C-A

DESCRIPTION

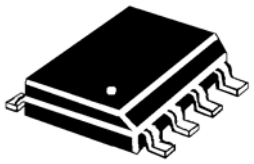
This Transient Voltage Suppressor (TVS) array is packaged in an SO-8 configuration giving protection to 2 Bidirectional data or interface lines. It is designed for use in applications where very low capacitance protection is required at the board level from voltage transients caused by electrostatic discharge (ESD) as defined in IEC 61000-4-2, electrical fast transients (EFT) per IEC 61000-4-4 and effects of secondary lightning. It is also available with either Tin-Lead plated terminations or as RoHS Compliant with annealed matte-Tin finish by adding an "e3" suffix to the part number*.

Using the schematic on the second page, pins 1 & 2 are tied together for the first protected line, and pins 7 & 8 are tied together to the ground. The same would then occur for a second protected line where pins 3 & 4 are tied together and pins 5 & 6 are tied together to the ground. These may also be switched in polarity connections since the electrical features are the same in each antiparallel (opposite facing) leg when the pins are tied together in this manner for bidirectional protection.

These TVS arrays have a peak power rating of 500 watts for an 8/20 μsec pulse. This array is suitable for protection of sensitive circuitry consisting of TTL, CMOS DRAM's, SRAM's, HCMOS, HSIC microprocessors, **UNIVERSAL SERIAL BUS (USB)** and I/O transceivers. The USB08XXC-A product provides board level protection from static electricity and other induced voltage surges that can damage or upset sensitive circuitry.

IMPORTANT: For the most current data, consult *MICROSEMI's* website: http://www.microsemi.com

APPEARANCE



SO–8

FEATURES

- Protects up to 2 bi-directional lines
- Surge protection per IEC 61000-4-2, IEC 61000-4-4
- Provides electrically isolated protection
- UL 94V-0 Flammability Classification
- RoHS Compliant devices available by adding "e3" suffix
- ***LOW CAPACITANCE 5 pF per line pair***
- ***LOW LEAKAGE***

APPLICATIONS / BENEFITS

- EIA-RS485 data rates: 5 Mbs
- 10 Base T Ethernet
- USB date rate: 900 Mbs
- Tape & Reel per EIA Standard 481
- 13 inch reel; 2,500 pieces (OPTIONAL)
- Carrier tubes; 95 pcs (STANDARD)

MAXIMUM RATINGS

- Operating Temperature: -55°C to +150°C
- Storage Temperature: -55°C to +150°C
- Peak Pulse Power: 500 watts (8/20 μs, Figure 1)
- Pulse Repetition Rate: < .01%
- Solder Temperature: 260°C for 10 s (maximum)

MECHANICAL AND PACKAGING

- Molded SO-8 Surface Mount
- Weight 0.066 grams (approximate)
- Marking: Logo, device marking code*, date code
- Pin #1 defined by dot on top of package

ELECTRICAL CHARACTERISTICS

PART NUMBER	DEVICE MARKING*	STAND OFF VOLTAGE V_{WM} VOLTS	BREAKDOWN VOLTAGE V_{BR} @1 mA VOLTS	CLAMPING VOLTAGE V_C @ 1 Amp (Figure 2) VOLTS	CLAMPING VOLTAGE V_C @ 5 Amp (Figure 2) VOLTS	STANDBY CURRENT I_D @ V_{WM} μA	CAPACITANCE (f=1 MHz) C @0V pF	TEMPERATURE COEFFICIENT OF V_{BR} α_{VBR} mV/°C
		MAX	MIN	MAX	MAX	MAX	MAX	MAX
USB0803C-A	U3CA	3.3	4	8	11	200	5	-5
USB0805C-A	U5CA	5.0	6.0	10.8	13	40	5	1
USB0812C-A	U12CA	12.0	13.3	19	26	1	5	8
USB0815C-A	U15CA	15.0	16.7	24	32	1	5	11
USB0824C-A	U24CA	24.0	26.7	43	57	1	5	28

***** Device marking has an e3 suffix added for RoHS Compliant option, e.g. U3CAe3, U5CAe3, U12CAe3, U15CAe3, or U24CAe3

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SYMBOLS & DEFINITIONS

Symbol	Definition
V_{WM}	Stand Off Voltage: Maximum dc voltage that can be applied over the operating temperature range. Vwm must be selected to be equal or be greater than the operating voltage of the line to be protected.
V_{BR}	Minimum Breakdown Voltage: The minimum voltage the device will exhibit at a specified current
V_C	Clamping Voltage: Maximum clamping voltage across the TVS device when subjected to a given current at a pulse time of 20 µs.
I_D	Standby Current: Leakage current at $V_{WM.}$
C	Capacitance: Capacitance of the TVS as defined @ 0 volts at a frequency of 1 MHz and stated in picofarads.

GRAPHS

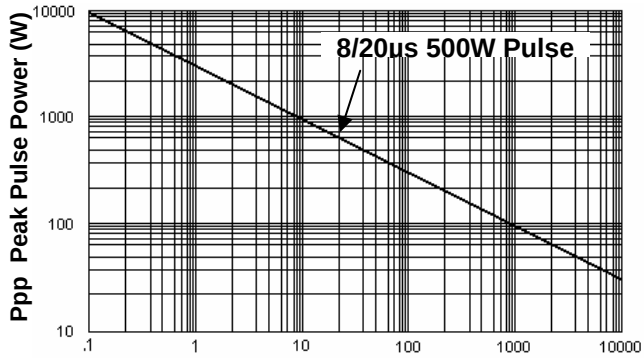


Figure 1
Peak Pulse Power Vs Pulse Time t = µsec

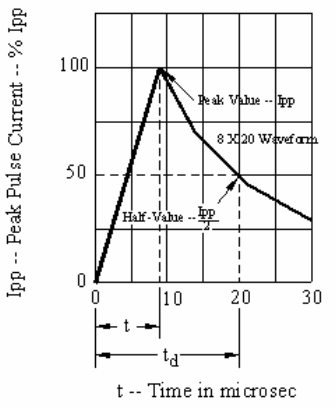
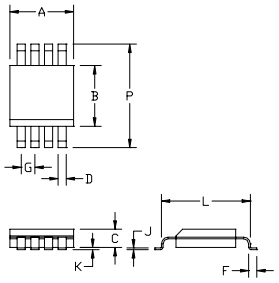


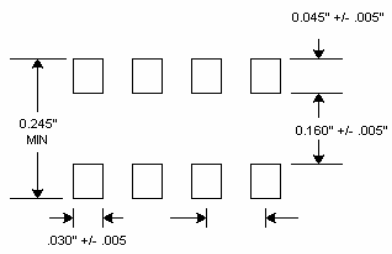
Figure 2
Pulse Wave Form

OUTLINE AND SCHEMATIC

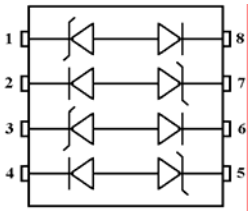


DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.188	0.197	4.77	5.00
B	0.150	0.158	3.81	4.01
C	0.053	0.069	1.35	1.75
D	0.011	0.021	0.28	0.53
F	0.0160	0.050	0.41	1.27
G	0.050 BSC		1.27 BSC	
J	0.006	0.010	0.15	0.25
K	0.004	0.008	0.10	0.20
L	0.189	0.206	4.80	5.23
P	0.228	0.244	5.79	6.19

OUTLINE



PAD LAYOUT



SCHEMATIC